

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- 9.5kV Internal Isolation
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM400GDM33-F032 is a single switch 3300V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM400GDM33-F032

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.8V
I_C (max)	400A
$I_{C(PK)}$ (max)	800A

* Measured at the auxiliary terminals

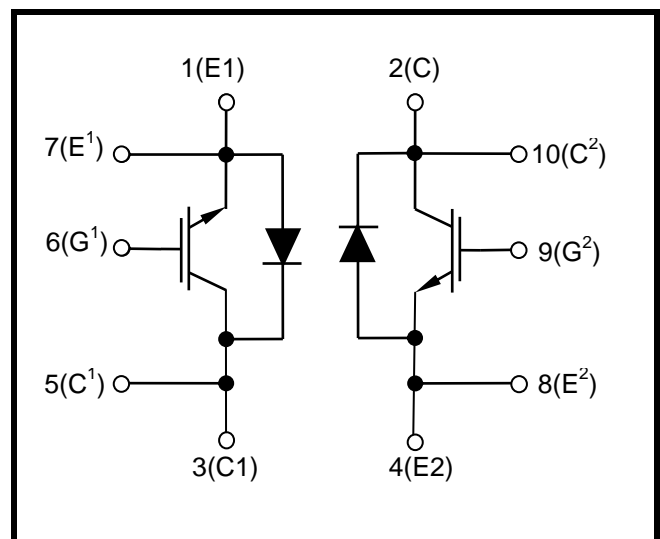


Fig. 1 Circuit configuration



Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	3300	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 90^{\circ}\text{C}$	400	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	800	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	5.2	kW
I^2t	Diode I^2t value	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	80	kA^2s
V_{isol}^*	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	9500	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 6400\text{V}$, $V_2 = 4700\text{V}$, 50Hz RMS	10	pC

* Package external clearances may not conform to all 9.5kV isolation standards.
Minimum external creepage/clearance distance between terminals and base plate is 33mm

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	350

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	24	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation - junction to case	-	-	48	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
 $T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			2	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125^{\circ}C$			30	mA
I_{GES}	Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			1	μA
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 40mA, V_{GE} = V_{CE}$	5.5	6.5	7.0	V
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 400A$		2.8		V
		$V_{GE} = 15V, I_C = 400A, T_j = 125^{\circ}C$		3.6		V
I_F	Diode forward current	DC		400		A
I_{FM}	Diode maximum forward current	$t_p = 1ms$		800		A
V_F^{\dagger}	Diode forward voltage	$I_F = 400A$		2.9		V
		$I_F = 400A, T_j = 125^{\circ}C$		3.0		V
C_{ies}	Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		72		nF
Q_g	Gate charge	$\pm 15V$		10		μC
C_{res}	Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		1.1		nF
L_M	Module inductance			25		nH
R_{INT}	Internal transistor resistance			260		$\mu\Omega$
SC_{Data}	Short circuit current, I_{SC}	$T_j = 125^{\circ}C, V_{CC} = 2500V$ $t_p \leq 10\mu s, V_{GE} \leq 15V$ $V_{CE(max)} = V_{CES} - L^* \times di/dt$ IEC 60747-9		1850		A

Note:
 \dagger Measured at the power busbars, not the auxiliary terminals

 $*$ L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 400\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{G(\text{ON})} = 8.2\ \Omega$ $R_{G(\text{OFF})} = 5.6\ \Omega$ $C_{ge} = 110\text{nF}$ $L_S \sim 100\text{nH}$		2100		ns
t_f	Fall time			210		ns
E_{OFF}	Turn-off energy loss			520		mJ
$t_{d(\text{on})}$	Turn-on delay time			1130		ns
t_r	Rise time			245		ns
E_{ON}	Turn-on energy loss			620		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 400\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 2000\text{A}/\mu\text{s}$		160		μC
I_{rr}	Diode reverse recovery current			330		A
E_{rec}	Diode reverse recovery energy			150		mJ

$T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 400\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{G(\text{ON})} = 8.2\ \Omega$ $R_{G(\text{OFF})} = 5.6\ \Omega$ $C_{ge} = 110\text{nF}$ $L_S \sim 100\text{nH}$		2150		ns
t_f	Fall time			220		ns
E_{OFF}	Turn-off energy loss			600		mJ
$t_{d(\text{on})}$	Turn-on delay time			1160		ns
t_r	Rise time			285		ns
E_{ON}	Turn-on energy loss			870		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 400\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 2000\text{A}/\mu\text{s}$		300		μC
I_{rr}	Diode reverse recovery current			400		A
E_{rec}	Diode reverse recovery energy			300		mJ

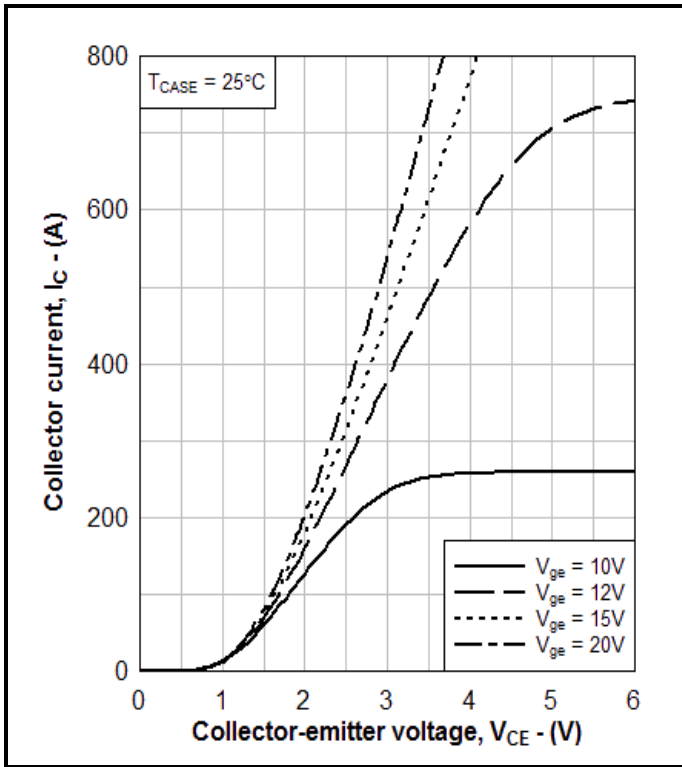


Fig. 3 Typical output characteristics

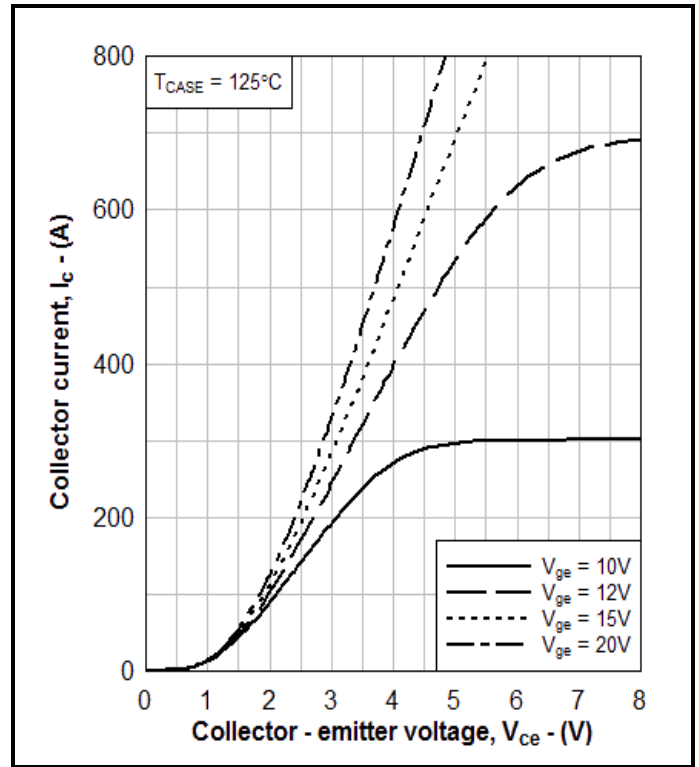


Fig. 4 Typical output characteristics

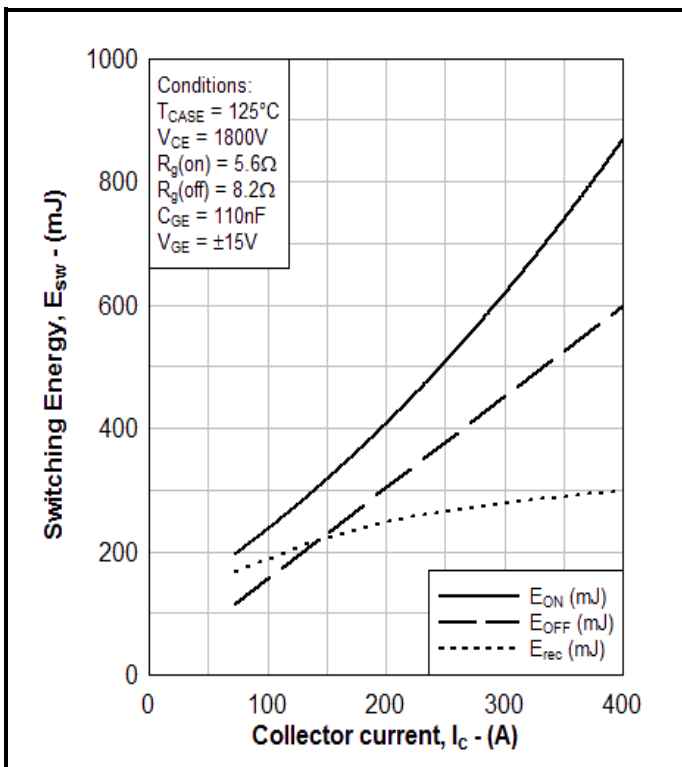


Fig. 5 Typical switching energy vs collector current

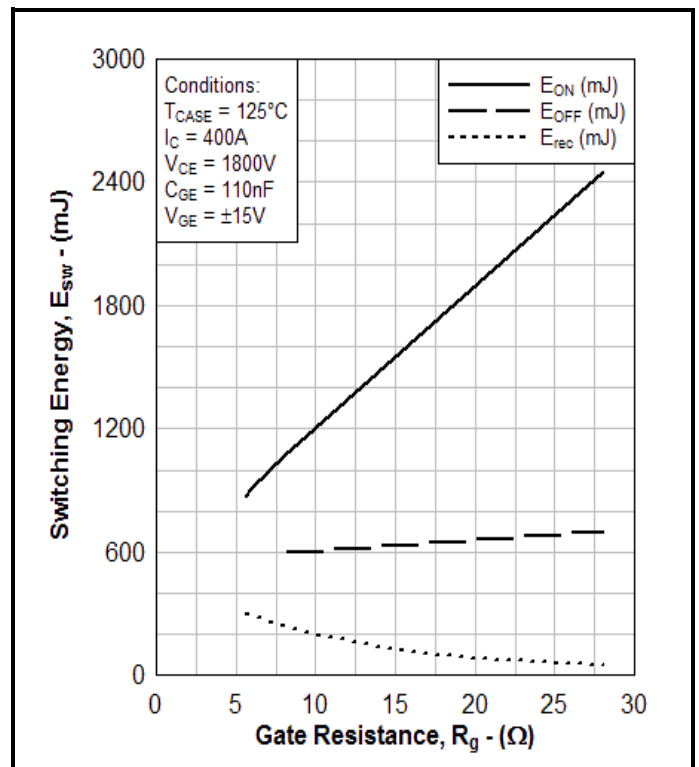


Fig. 6 Typical switching energy vs gate resistance

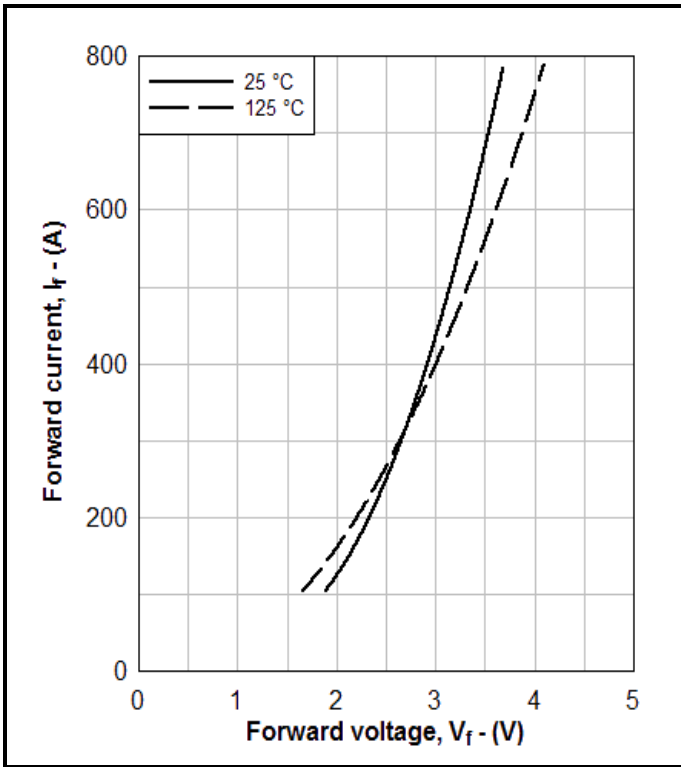


Fig. 7 Diode typical forward characteristics

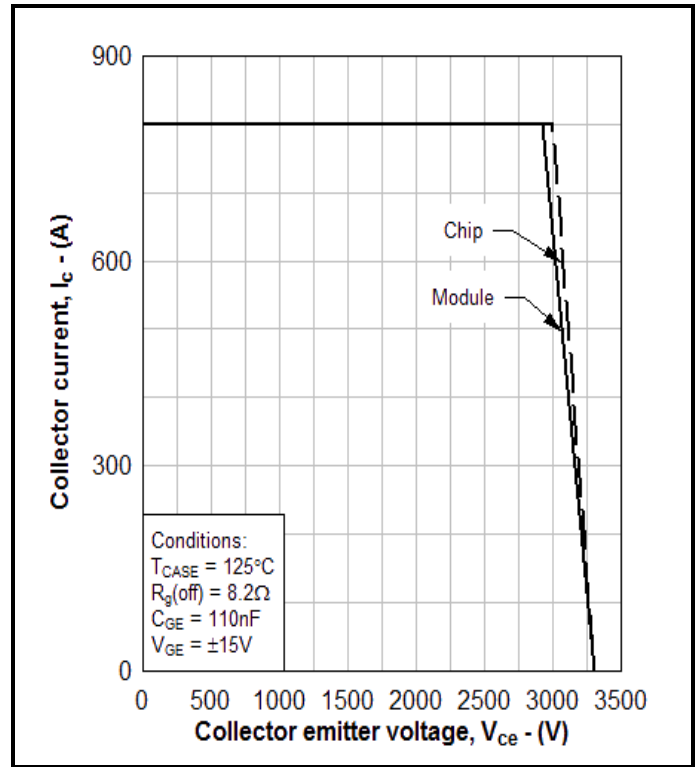


Fig. 8 Reverse bias safe operating area

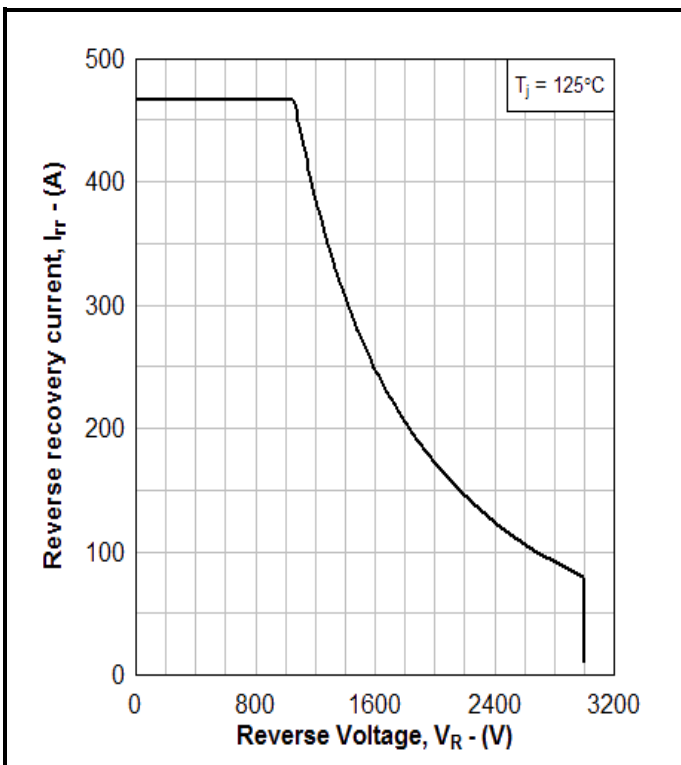


Fig. 9 Diode reverse bias safe operating area

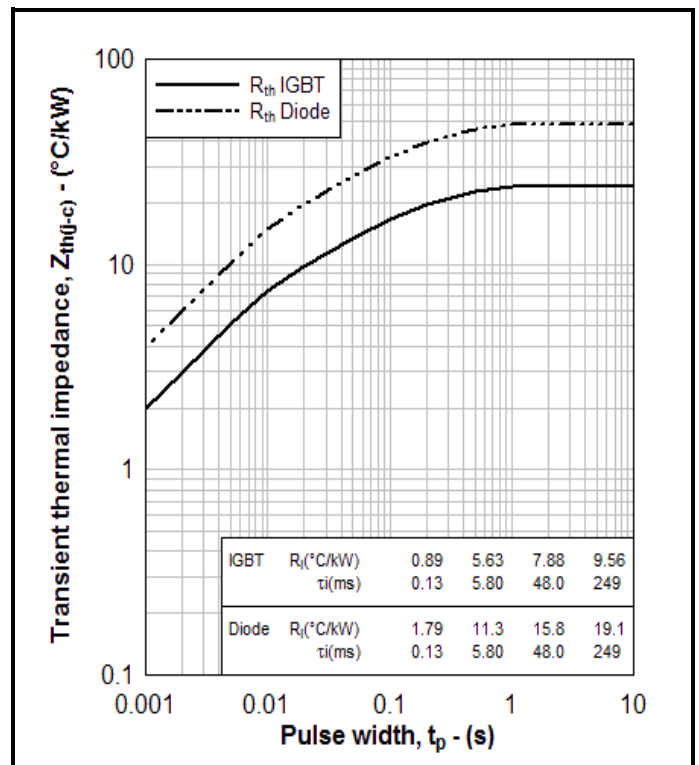
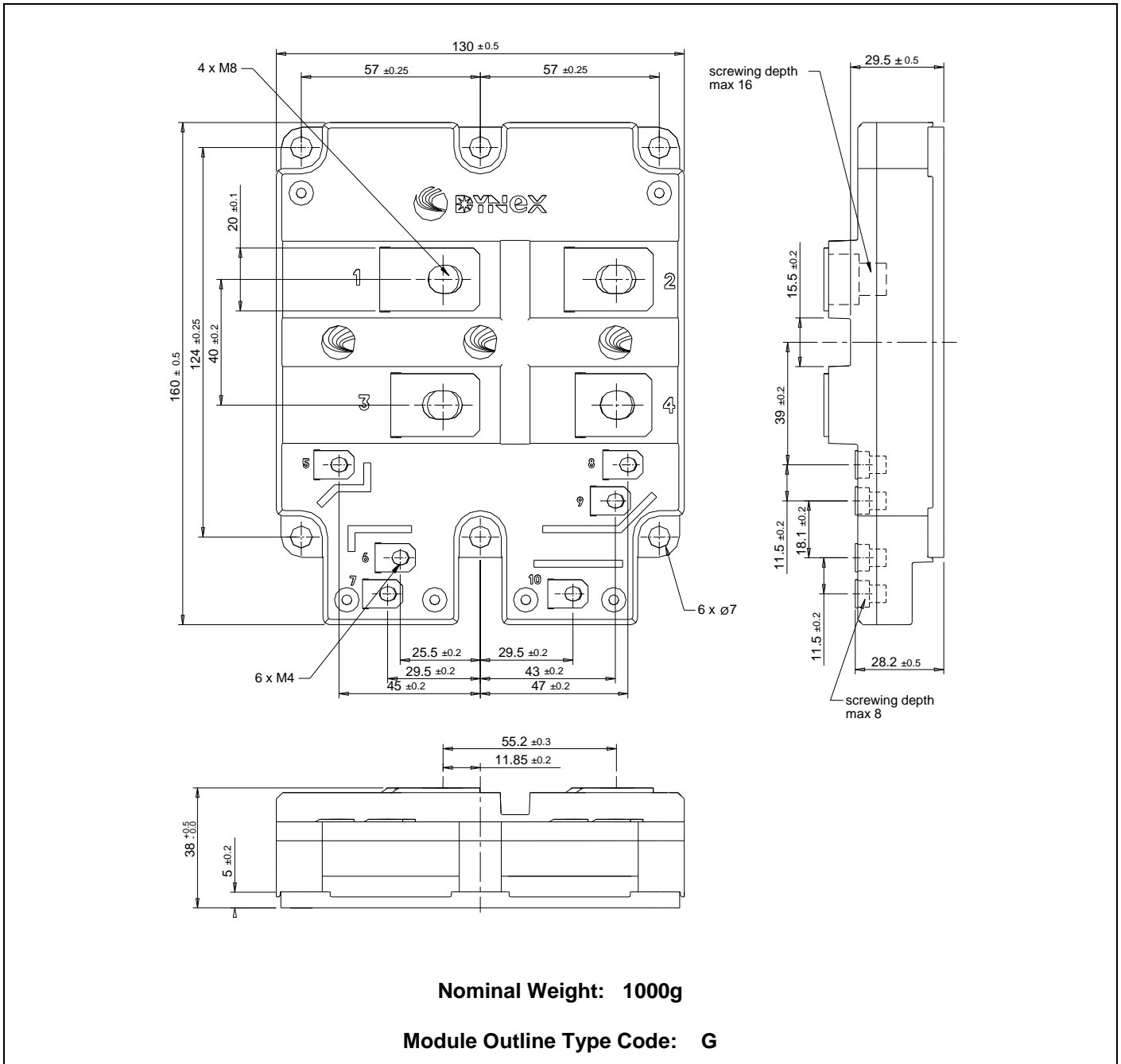


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 1000g

Module Outline Type Code: G

Fig. 11 Module outline drawing

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